

Status of LArG DMILL chips

C. de LA TAILLE

LAL Orsay

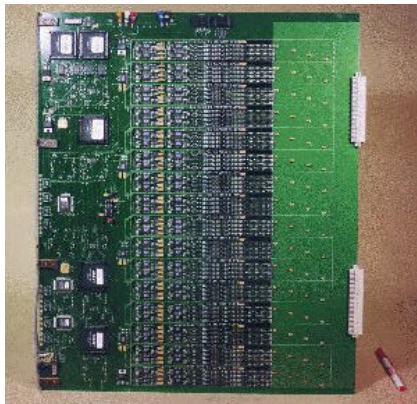
on behalf of the LArG collaboration



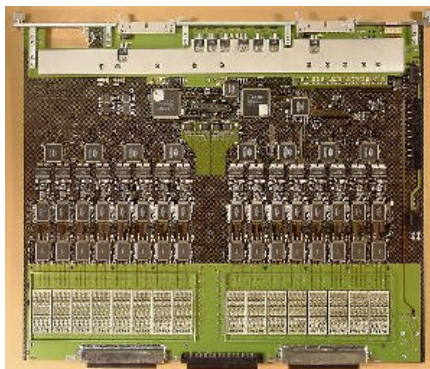
<http://www.lal.in2p3.fr/recherche/atlas>

Liquid Argon front-end electronics overview

[LEB6 p.265]



Calibration :
116 boards @ 128 ch

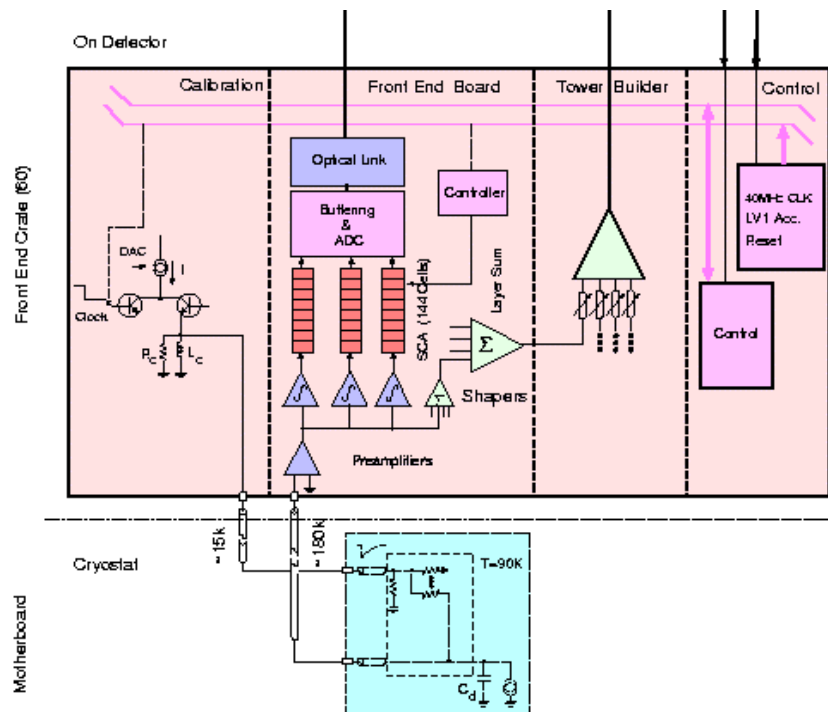


Front End Board (FEB) :
1524 boards @ 128 ch

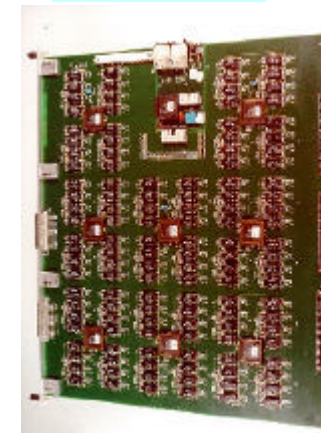
12 sept 2001

On-detector electronics

- Boards tested functionally on mod 0
- ATLAS *rad-tol* boards being finalized



Controller :
116 boards



Tower builder (TBB) :
120 boards @ 32 ch

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Radiation maps

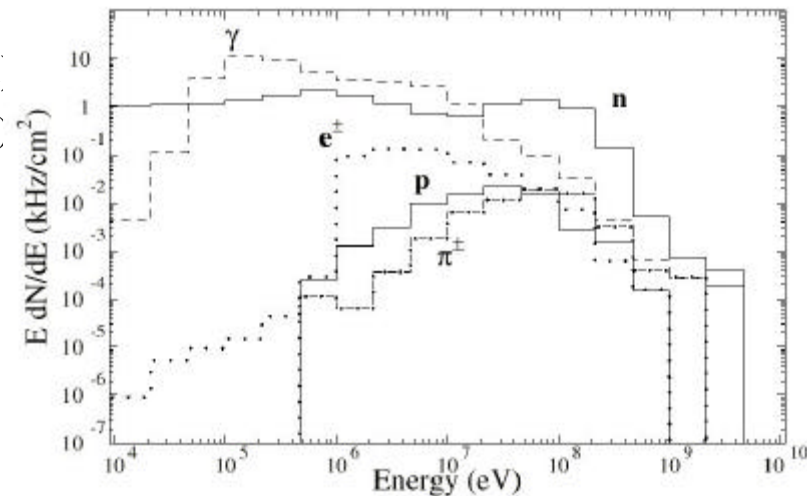
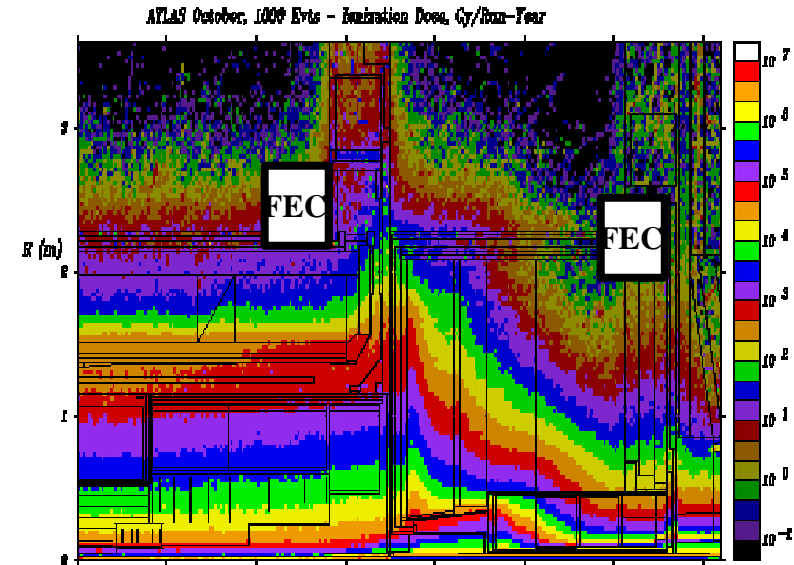
[LEB6 p.270]

■ Radiation levels for LAr crates

- barrel (in 10 yrs) :
 - TID = 50 Gy/10yr
 - NIEL = $1.6 \cdot 10^{12}$ N/cm²/10yr
 - SEE = $7.7 \cdot 10^{11}$ h/cm²/10yr (>20 MeV)

■ Radiation Tolerance Criteria (RTC) for DMILL chips (includes SF)

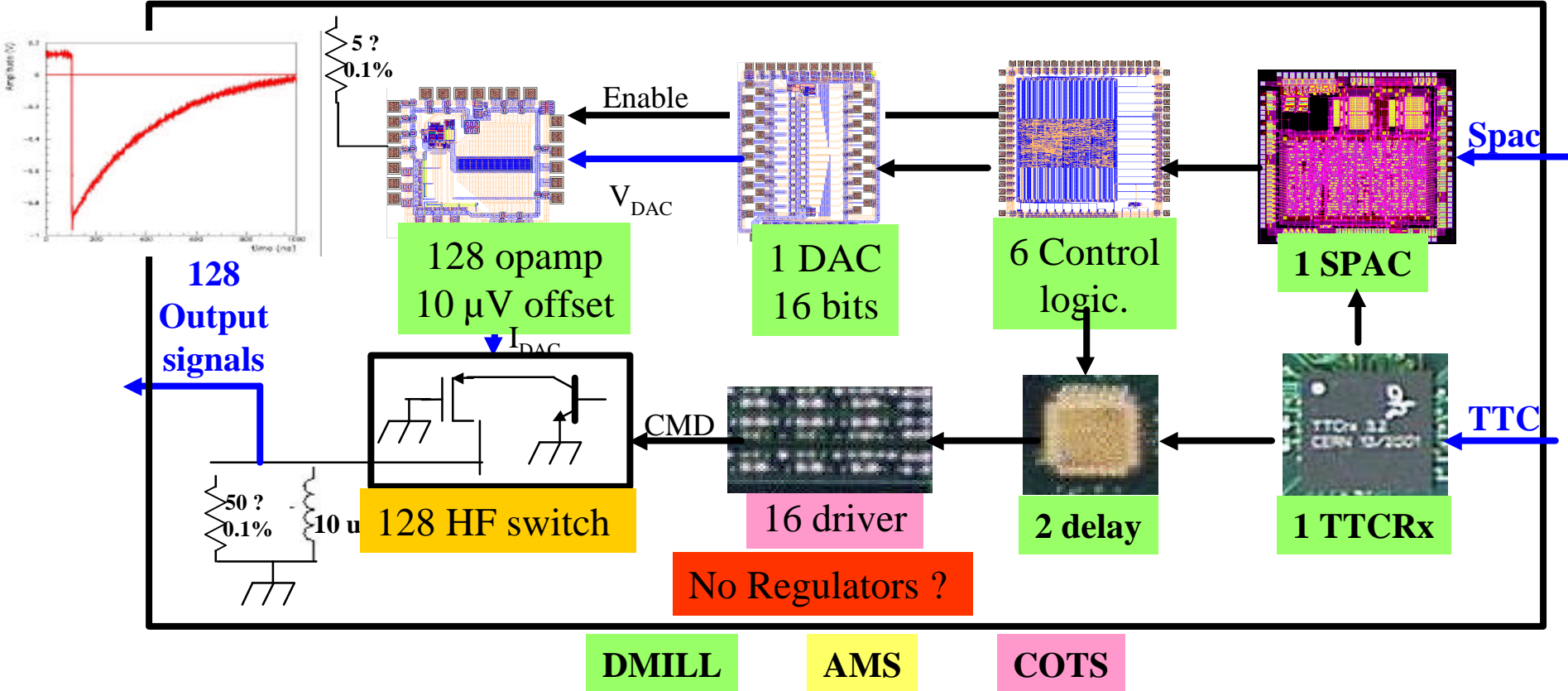
- TID = 50 * 3.5 (simul) * 1.5 (ldr) * 2 (lot)
= 525 Gy/10yr (3.5 kGy for COTS)
- NIEL = $1.6 \cdot 10^{12}$ * 5 (simul) * 1 (ldr) * 2 (lot)
= $1.6 \cdot 10^{13}$ N/cm²/10yr (3.2 $\cdot 10^{13}$ for COTS)
- SEE = $7.7 \cdot 10^{11}$ * 5 (simul) * 1 (ldr) * 2 (lot)
= $7.7 \cdot 10^{12}$ h/cm²/10yr
- Irradiation tests are *mandatory* for final qualification and still *recommended* for production batches



Calibration Board : overview

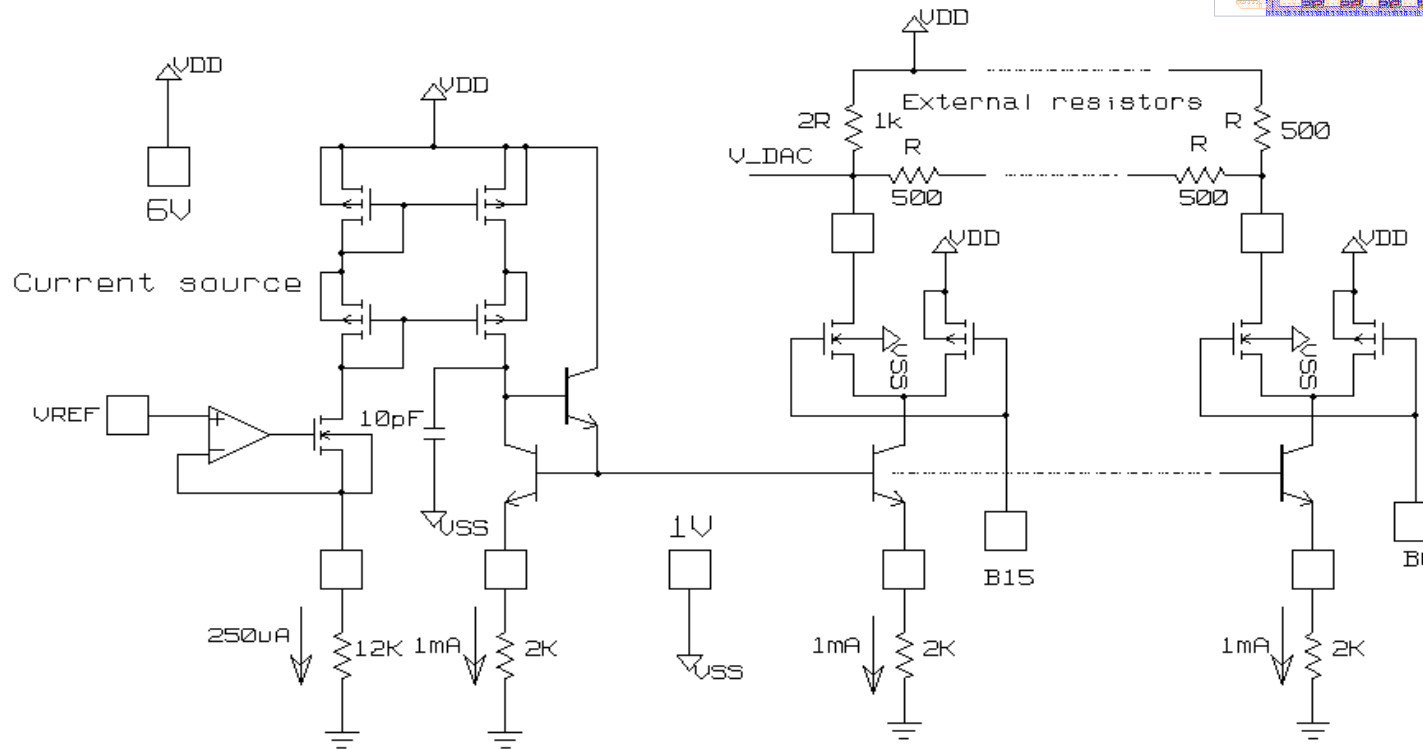
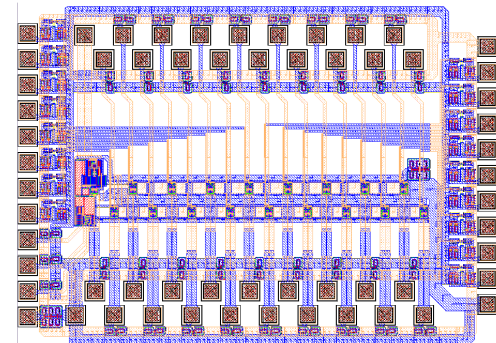
[LArG 2000-006]

- **Generate 0.2% precision calibration pulses** (Annecy, Mainz, Orsay)
 - Milestones : * Final prototype : Apr 02
 - * Production of 130 boards : Apr 03
 - * Installation complete Feb 05



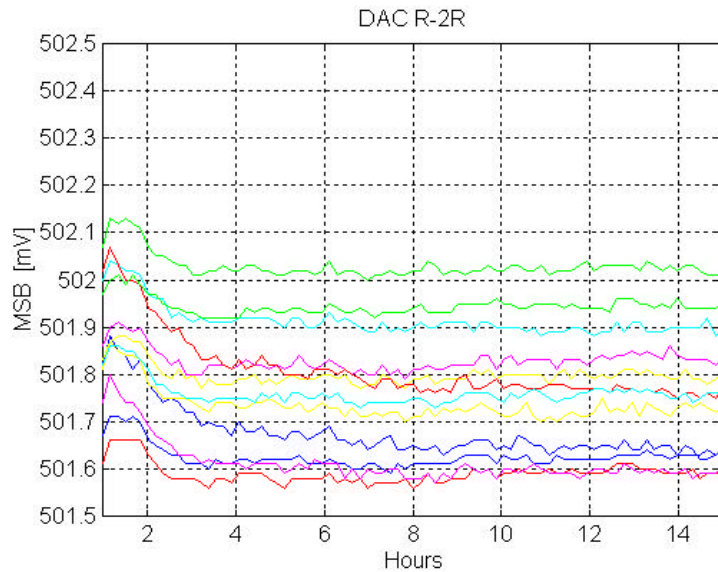
Calib : DAC design

- **16 bit DAC : DMILL (Orsay)**
 - **COTS failed** irradiation tests at 20 Gy
 - **16 bits** dynamic range (16 μ V-1V), 10 bits accuracy (**0.1%**)
 - external **R/2R ladder** and highly degenerated current sources
 - Good stability at small DAC value



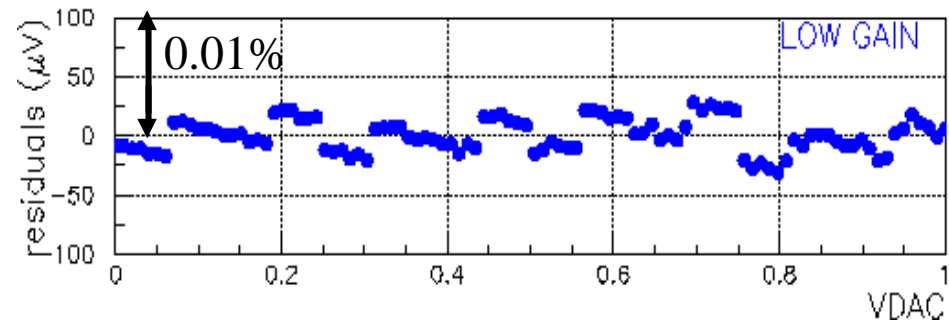
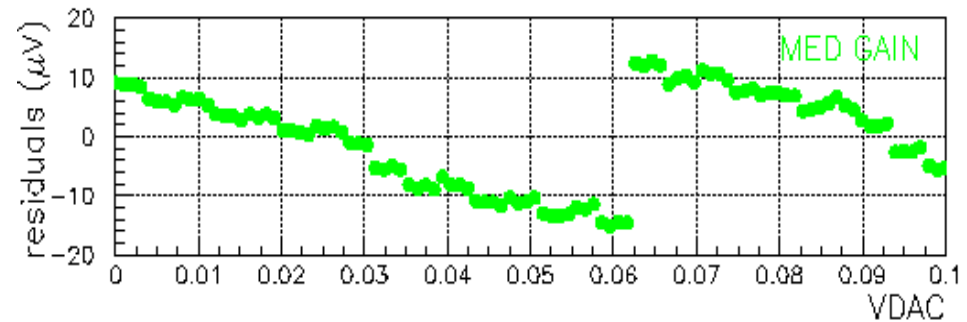
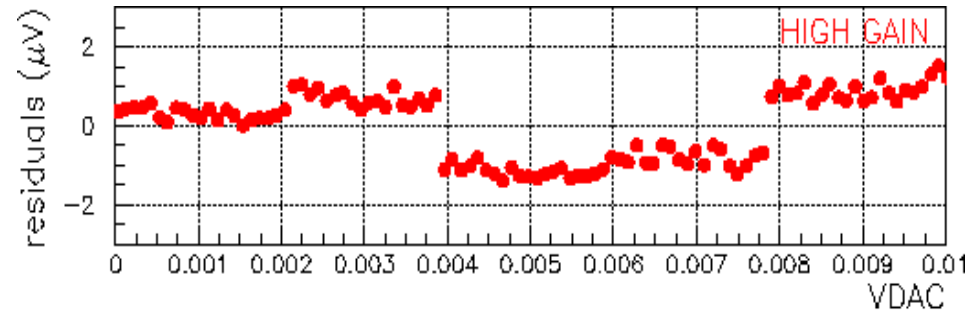
Calib : DAC performance

- **Yield :**
 - 6.3 mm² chip, received Mar 01
 - yield : 94%
- **Performance :**
 - Accuracy : 0.01% or 10 μV
 - Linearity : INL < 0.01%
 - Stability : 0.01%/K
 - Settling time < 1 μs



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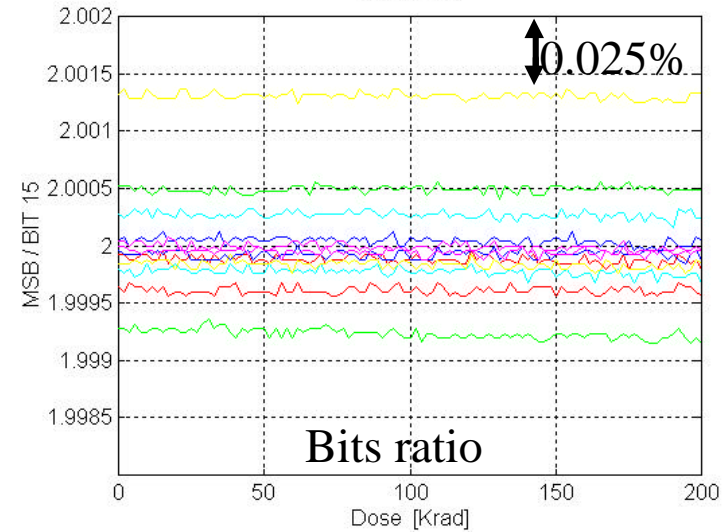
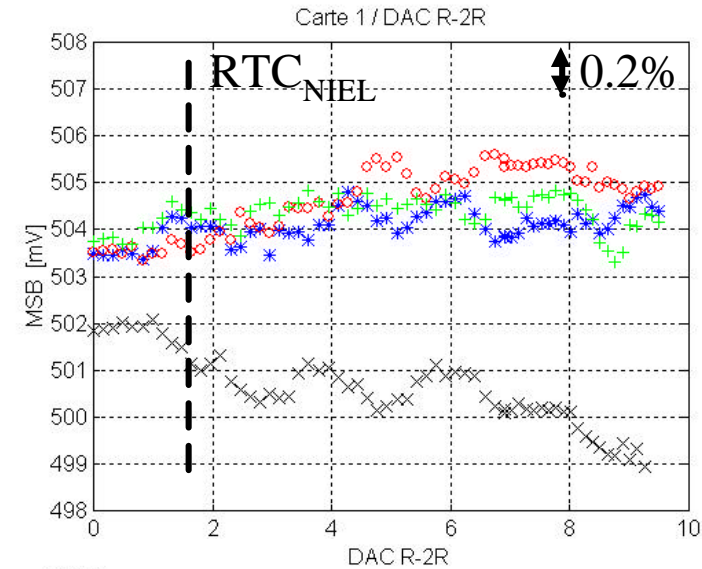
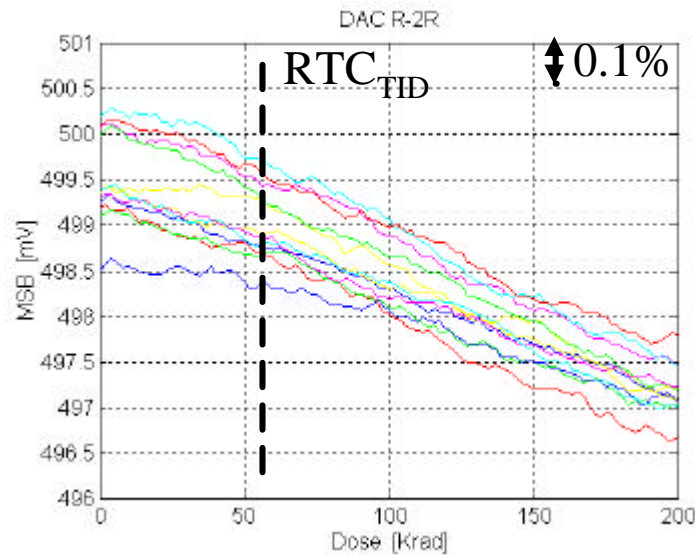


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Calib : DAC irradiation results

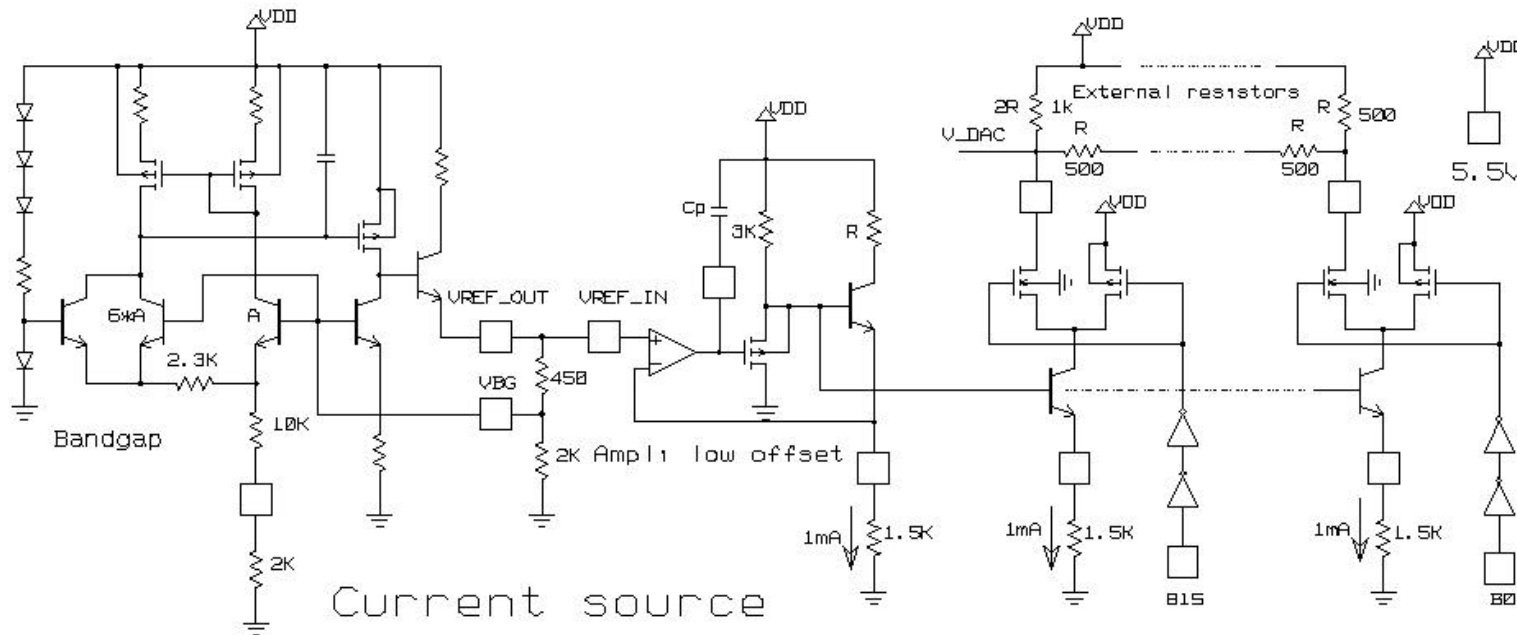
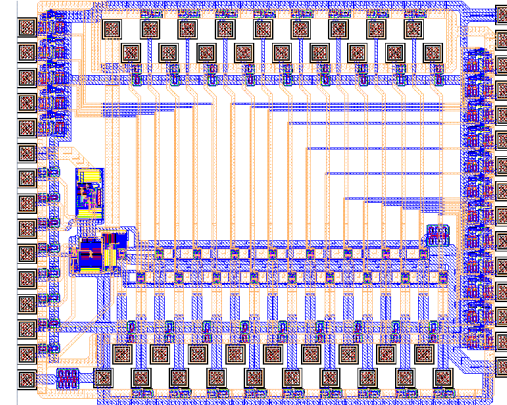
- **Neutrons : up to $9 \cdot 10^{13}$ at CERI**
 - No significant change
- **Gammas up to 2 kGy with ^{60}Co**
 - 0.5% overall change after 2 kGy
 - Global shift in current reference due to current mirror
 - V_T shift mismatch around 1 mV
 - Good annealing



Calib : DAC final version

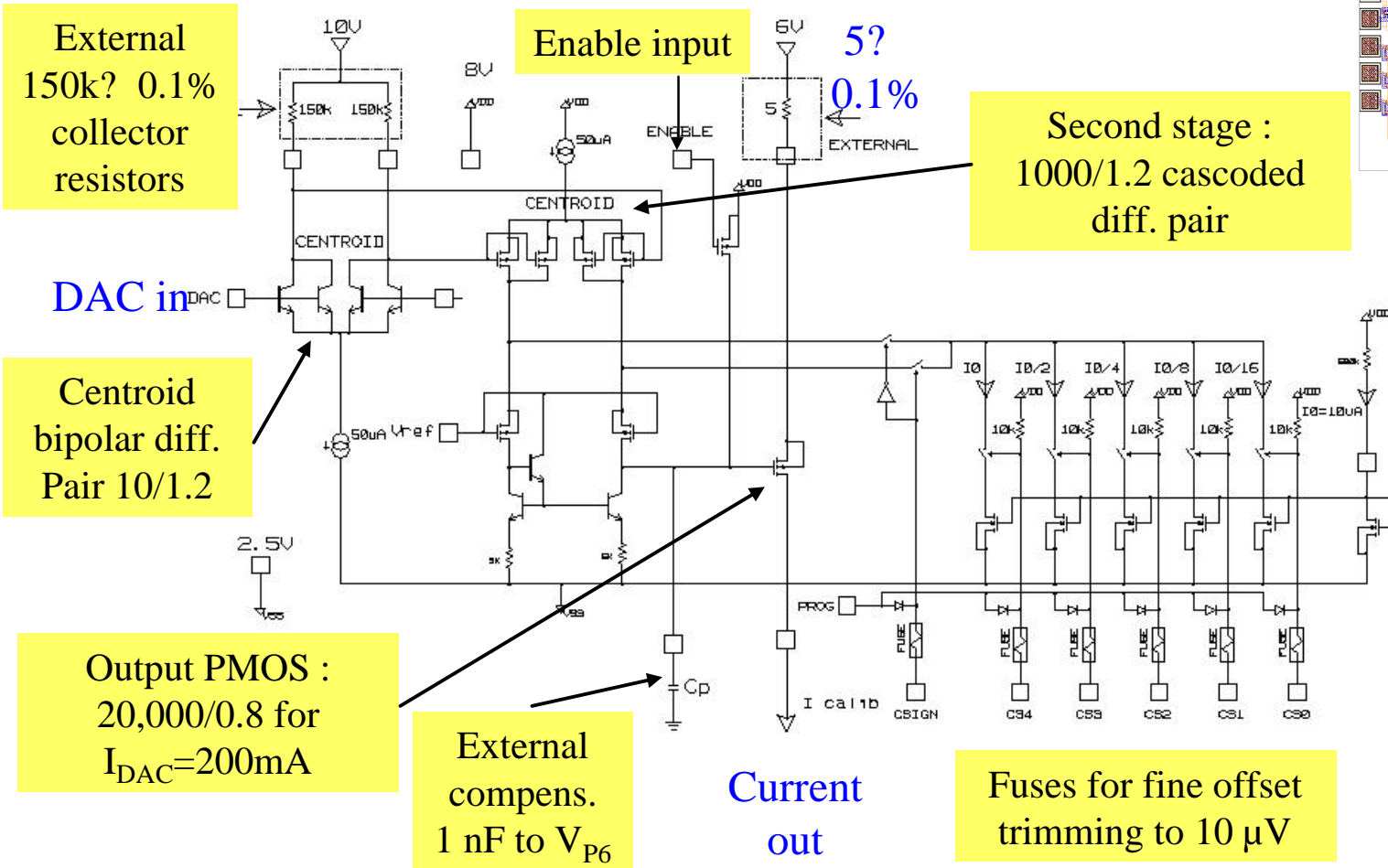
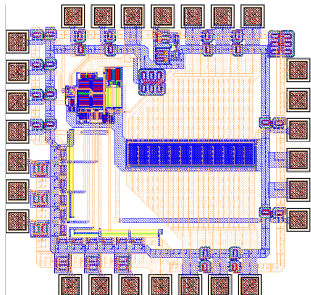
Final DAC prototype

- Band-gap reference voltage (1.5 V).
- Current mirror removed. Feedback on reference.
- Logic level translators inside
- Submitted in Sept 01, area : 8 mm²
- 1 DAC per board, 150 chips needed



Calib : low offset opamp design

- Used in 0.2% accuracy DC current source (2 μA-200 mA) (Orsay)



Calib : low offset opamp performance

■ Yield :

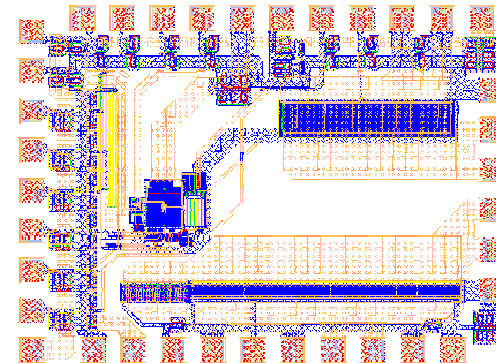
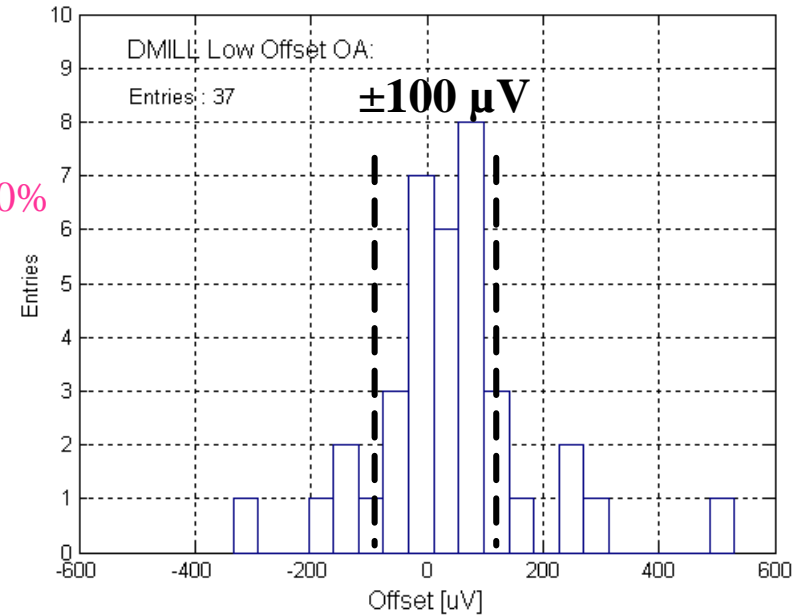
- 2 mm² chip, received March 01 (MPW 471).
- Fully functional. Yield : 92%
- Selection inside $\pm 100 \mu\text{V}$? sorting yield : 70%

■ Performance :

- Open loop gain 80,000
- GBW = 100 kHz
- Offset stability : a few μV
- Temperature sensitivity : $+1 \mu\text{V/K}$

■ Final iteration

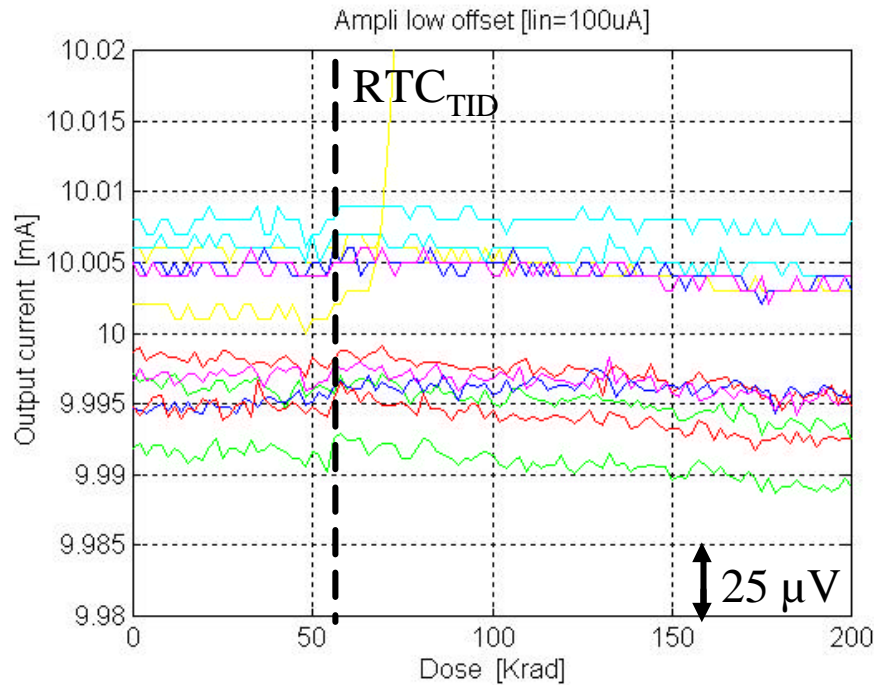
- Include HF switch (cost reduction)
- Opamp unchanged
- Chip submitted in May 01. Area : 3 mm²



Calib : low offset opamp irradiation results

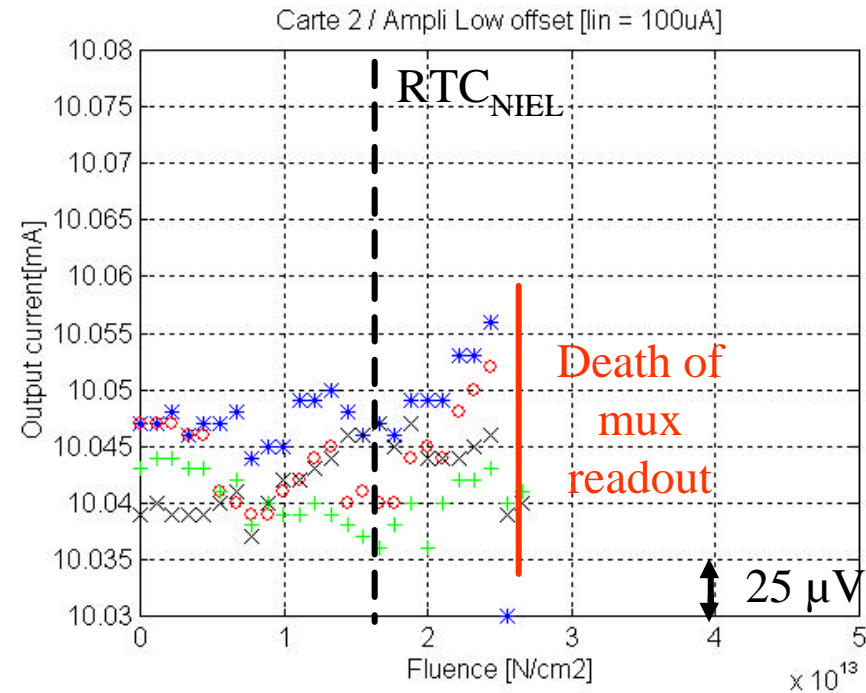
■ Gammas up to 2 kGy

- ^{60}Co at Pagure (Saclay)
- No change within 15 μV up to 200 krad



■ Neutrons up to 9 10^{13} N/cm²

- ~10 MeV neutrons at CERI (Orleans)
- Maximum change : 50 μV after 9 10^{13}
- Beta change (@ $I_C = 25 \mu\text{A}$) :
 - 180 prerad, 62 @ 510^{13} , 37 @ 9 10^{13}



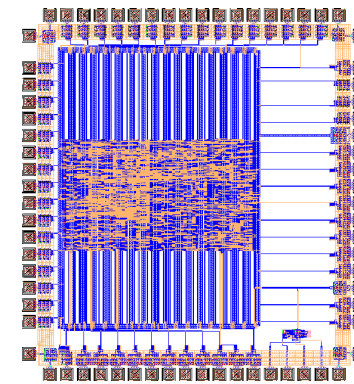
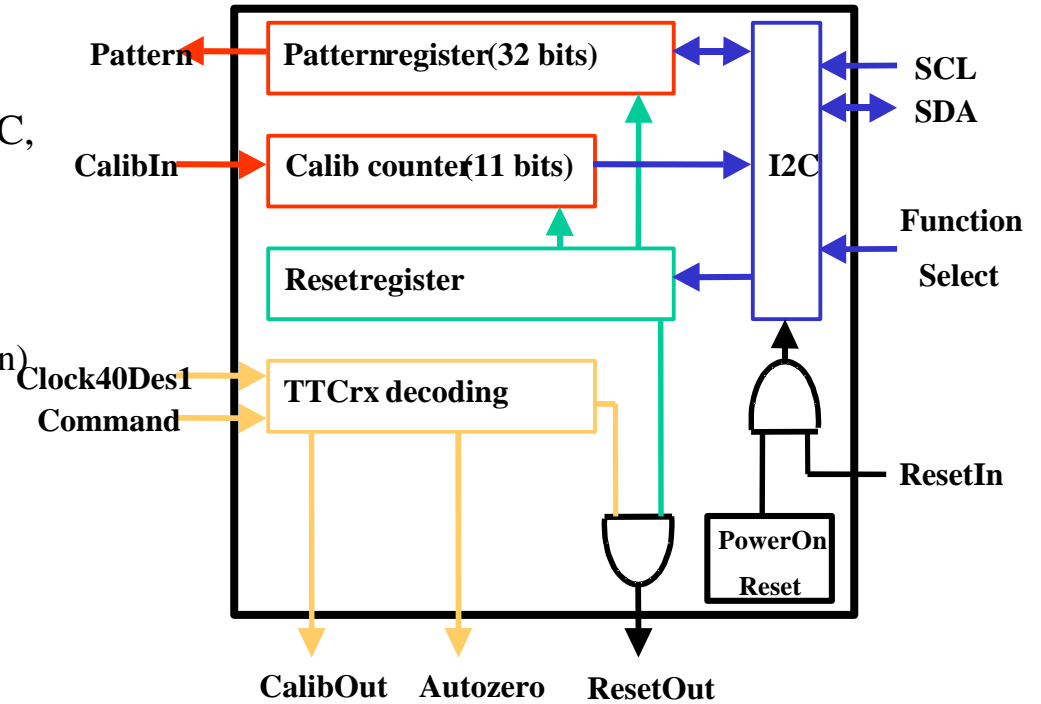
Calib : Digital chips

■ Control logic : DMILL (Annecy)

- Common DMILL chip to control DAC, pattern and delays registers
- 16 mm² chip, received Mar 01 (MPW 471). Yield : 80%
- SEE test performed in Apr 01 (Louvain)
 - no SEU up to $\sim 3 \cdot 10^{12}$ p⁺ (60 MeV)
 - In ATLAS < 2 SEU/yr
- Iterated in May 01 to correct initialization

■ Delay chip : DMILL (CERN)

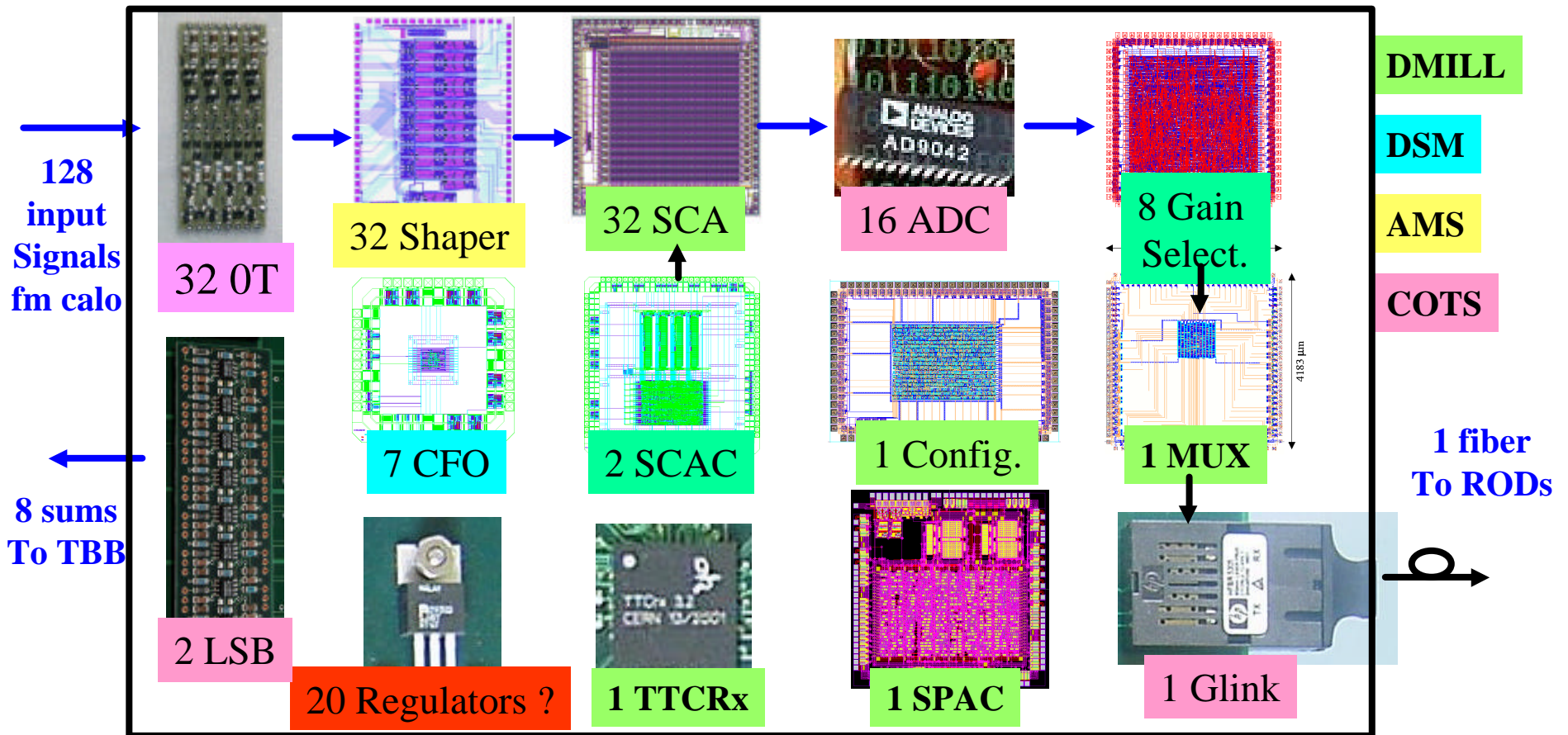
- 2 chips per board ? 260 chips required



Front End Board (FEB) : overview

- Amplification, shaping, analog storage and digitization (Nevis)

- Milestones : first final board : Oct 2001, 30 boards : Oct 2002, 1700 boards : Apr 2003

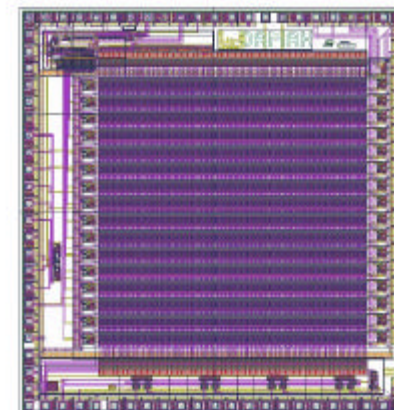


FEB : analog pipelines (SCA)

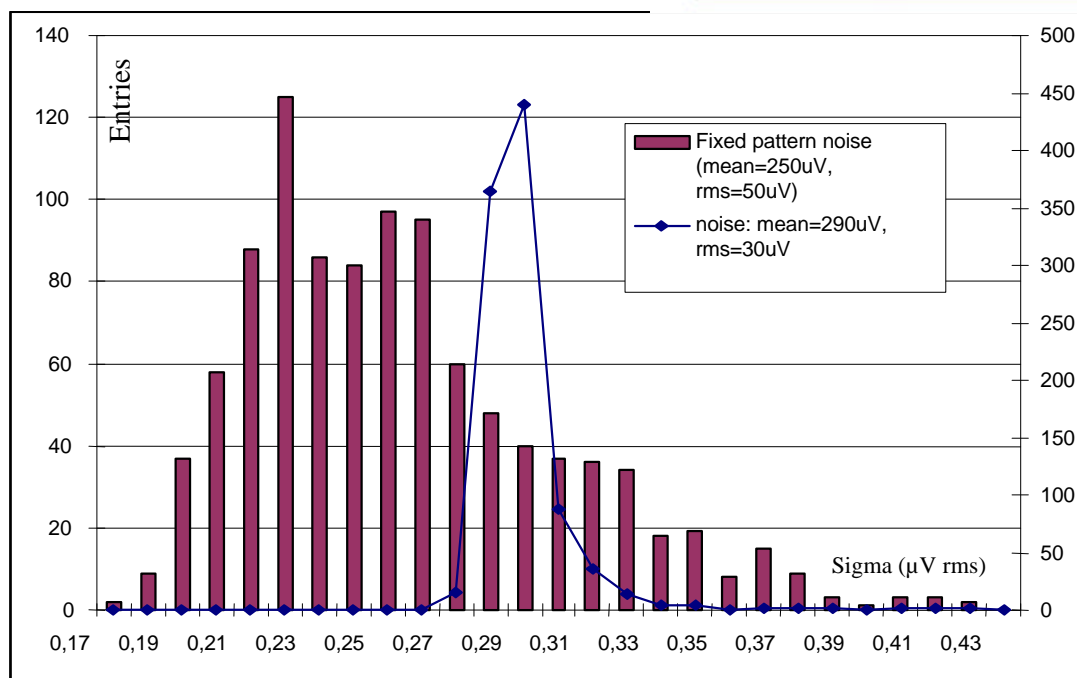
[LEB6 p.203]

■ SCA : DMILL CMOS chip (Nevis,Orsay,Saclay)

- 144 cells deep analog storage, 13 bit dynamic range
- 4 channels (3 gains + 1 reference) per chip. Dissipation 300 mW.
- Simultaneous Read/Write at 40 MHz. Output rate 5 MHz.
- Noise : 290 μV ; fixed pattern noise : 250 μV ; jitter < 70 ps
- Irradiation tests : OK
 - 3 kGy
 - $2 \cdot 10^{13}\text{N}$
 - no SEU tests
- Yield : 10-90%



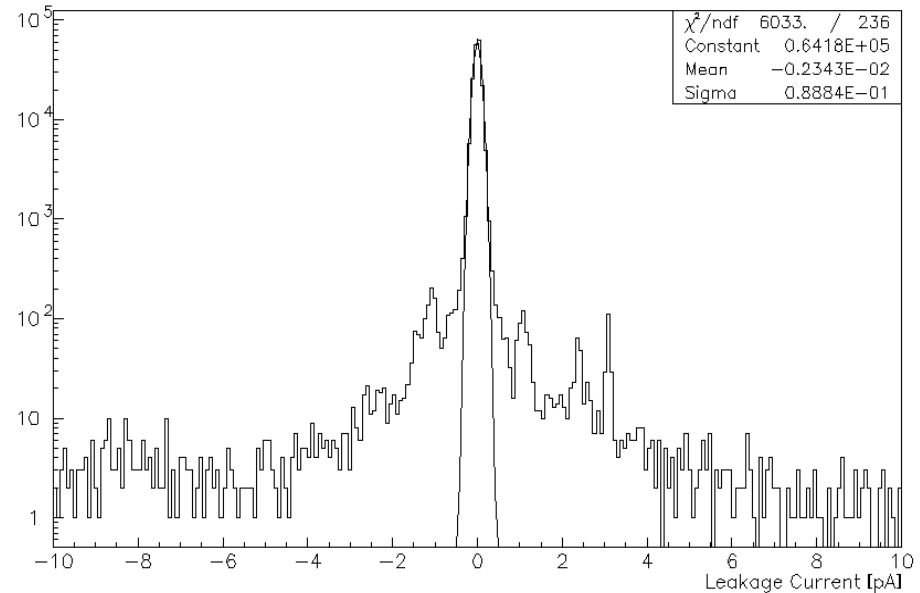
BATCH	DATE	YIELD
V 1.1	6 / 98	90 %
V 1.2	8 / 98	80 %
V 2 w12	8 / 99	50 %
V2 w4	8 / 99	84 %
V 3.1	10 / 99	10 %
V 3.2	7 / 00	65 %
V 4.1	3 / 01	60 %



FEB : DMILL SCA test results

■ Engineering run launched in nov 00

- 30 mm² chip; 416 chips/wafer
- 6 wafers received in march 2001, 2 more in july 01 (new batch)
- 2543 chips tested : raw yield : 69%
- Cut on leakage current : $I < 5 \text{ pA}$?
yield : 65%

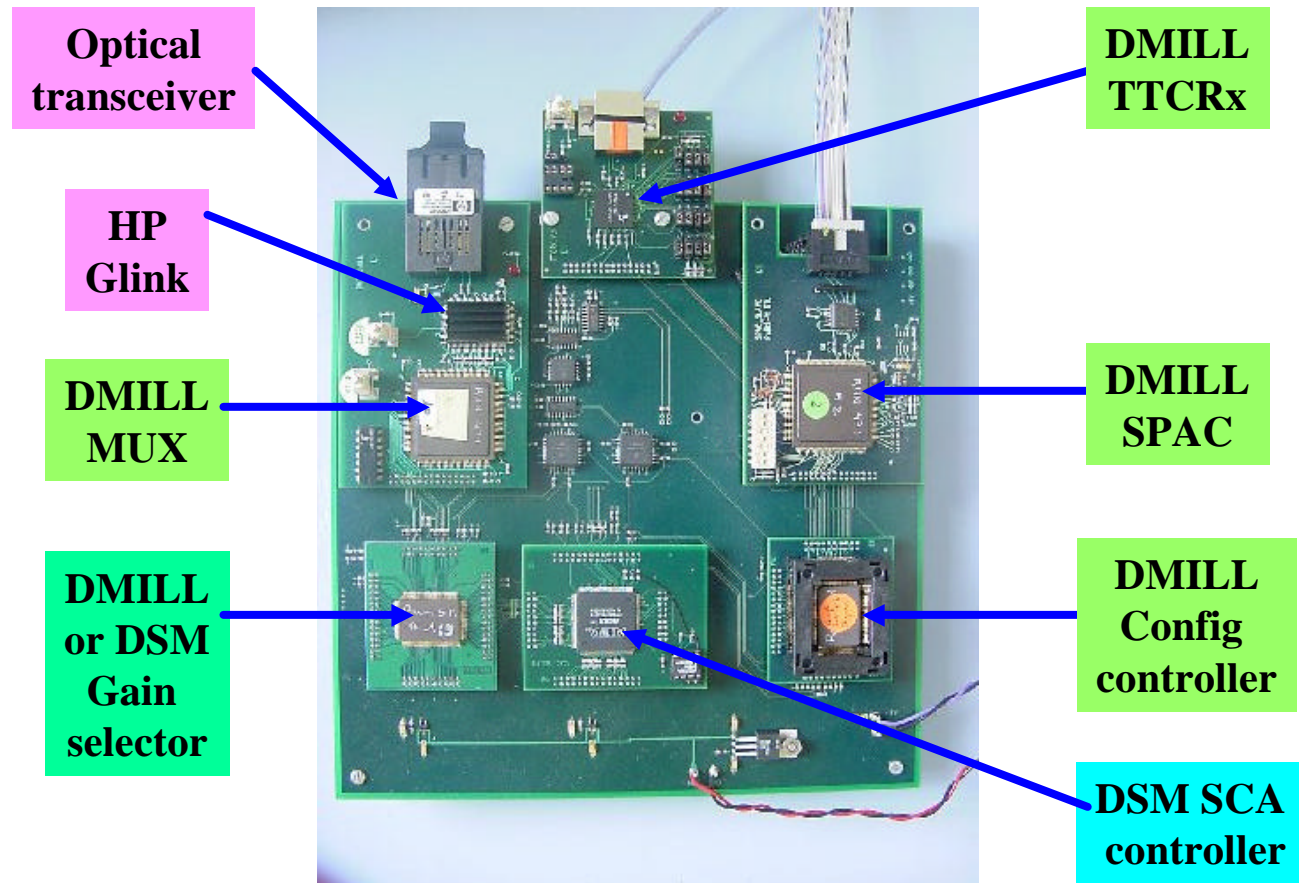


■ Production run : fall 2001

- 32 per FEB ? 54,000 chips needed
- 220-250 wafers (~ 1.5 M\$)
- PRR with Atmel : Oct 2001.
Define target yield
- Tests at Grenoble with robot : ~6 months

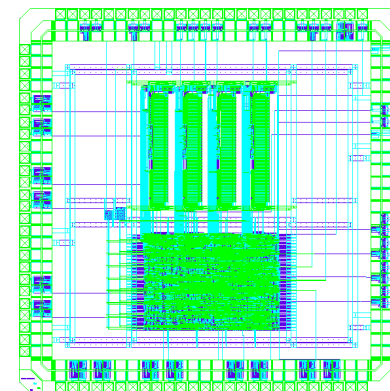
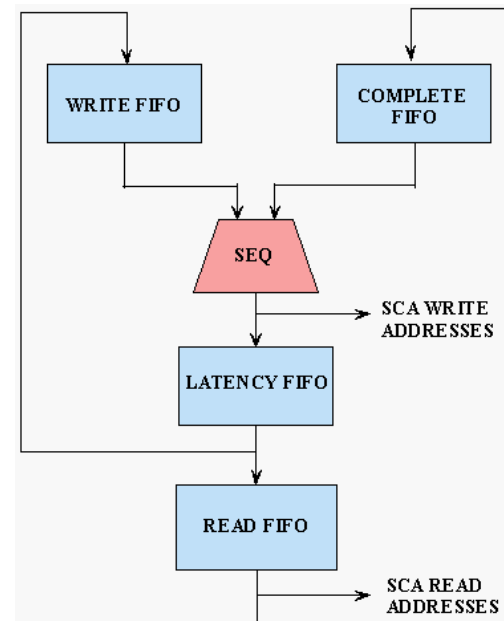
1/4 digital FEB

- **Test setup for all FEB digital ASICs** (Nevis)
 - Complete operation of SCAC, Gain selector, config contr., SPAC slave, TTCRx, MUX, Glink ? **Tests OK**



FEB : SCA controller (SCAC)

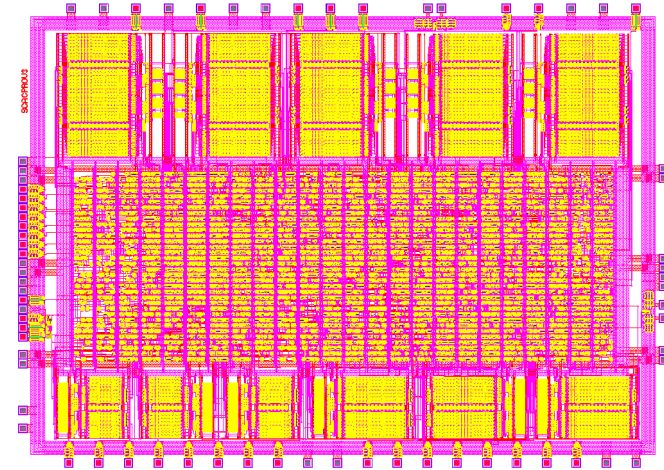
- **A very critical component (Alberta)**
 - Book-keeping of SCA addresses
 - Mod0 **Xilinx** (0.35 μm XC 4036) **failed** at 450 Gy
 - **SEU** cross-section : $s_{\text{SEU}} = 2.7 \cdot 10^{-9} \text{ cm}^2$ [LArG 2001-011]
 - LET for configuration switches : $22 \pm 2 \text{ MeV}$
 - **1 latch-up** @105MeV : $s_{\text{SEL}} = 8 \cdot 10^{-14} - 10^{-12} \text{ cm}^2$ (95% CL)
- **Difficult implementation in DMILL**
 - Special RAMs needed (CEA-DAM)
 - Large chip area (80 mm^2) ? **potentially low yield (20%)**
 - **SEU** : incorrect functioning until reset
 - no room for error detection/correction
 - Submitted Nov 00 (MPW 533), received July 01
- **Backup launched in DSM (0.25 μm) (Nevis)**
 - Smaller area (16 mm^2), higher yield, lower cost
 - **Error correction** implemented
 - Submitted Feb 01, received July 01.
- **In critical path if an iteration is needed**
 - 2 chips per FEB, 3 400 chips needed



FEB : DMILL SCAC test results

■ Yield (DMILL)

- 40 chips received july 01
- 28 good parts : preliminary yield : 70%
- Correct operation up to 50 MHz (9 chips tested)
- No failure after burn-in (7 chips tested)



■ SEU test results (Alberta)

- 4 chips irradiated to $3-6 \cdot 10^{11} \text{ p}^+/\text{cm}^2$ (74 MeV) (Triumf Aug 01)
- Associated TID : 30-80 krad
- Mean flux until upset : $4.6 \pm 0.2 \cdot 10^{10} \text{ p}^+/\text{cm}^2$. Power cycling needed to reset !
- Extrapolated to ATLAS as 1 SEU/SCAC/70days ? reset every hour
- Traced to “Power on reset” (analog) circuit, issuing continuous reset.
 - Failure probably due to TID effect
 - Removed externally
 - Further failures (with TID) of the input LVDS buffers

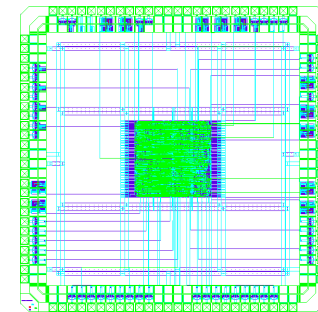
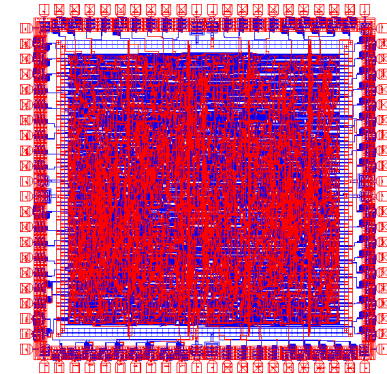
FEB : Gain selector

■ Gain selection and data formatting (Nevis)

- On chip storage of 16 thresholds values
- **SEU mitigation** : on chip bit error detection and correction
- **DMILL chip**
 - 21 mm² chip, received Mar 01. **yield : 93%**.
 - 581 chips per wafer, 34 wafers necessary : full engineering run.
- **DSM alternative**
 - 16 mm² chip, submitted in Feb 01, received Jun 01

■ SEE irradiation results (DMILL chip)

- 5 chips irradiated to 2-7 10¹³ p⁺ (50, 100, 158 MeV) (Harvard may 01)
- **SEE** : SBE (corrected) and SEU (? 1-2 events corrupted)
- Extrapolated rate to full calo : 1 SBE/30 min 1 SEU/168 min

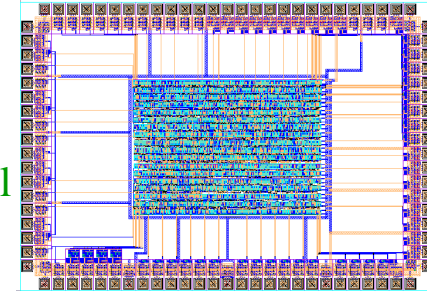


Energy (MeV)	Fluence (10 ¹³ /cm ²)	Single Bit Errors (SBE)		Single Event Upsets (SEU)	
		Number	σ (10 ⁻¹³ cm ²)	Number	σ (10 ⁻¹³ cm ²)
50	2.4	0	-	0	-
100	4.0	14	3.5	4	1.0
158	20.8	212	10.2	38	1.8

FEB : digital chips

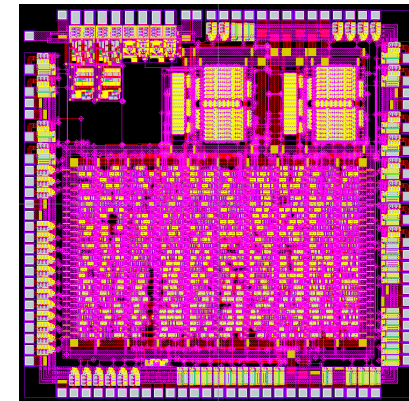
■ Config controller (Nevis)

- Interfaces SPAC to local busses (shaper, SCAC, regulators...)
- DMILL chip : 22 mm² area, received Mar 01 **yield : 93%. Final**
- **SEE** irradiation results (4 DMILL chips) 7-22 10¹³ p⁺ (158 MeV)
 - 69 SEU observed ? $s_{\text{SEU}} = 1.5 \cdot 10^{-13} \text{ cm}^2$
 - $R_{\text{SEU}} = 1 \text{ SEU}/26.8 \text{ hr}$ in ATLAS (2-15 Mrad associated TID)



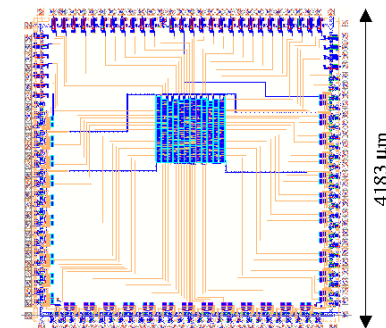
■ SPAC slave (Paris) [LEB6 p.454]

- Serial interface to write/read parameters. Manchester encoding
- 27 mm² DMILL chip, received Mar 01. **yield : 94%.**
- Iterated in sept 01 for **SEU mitigation**



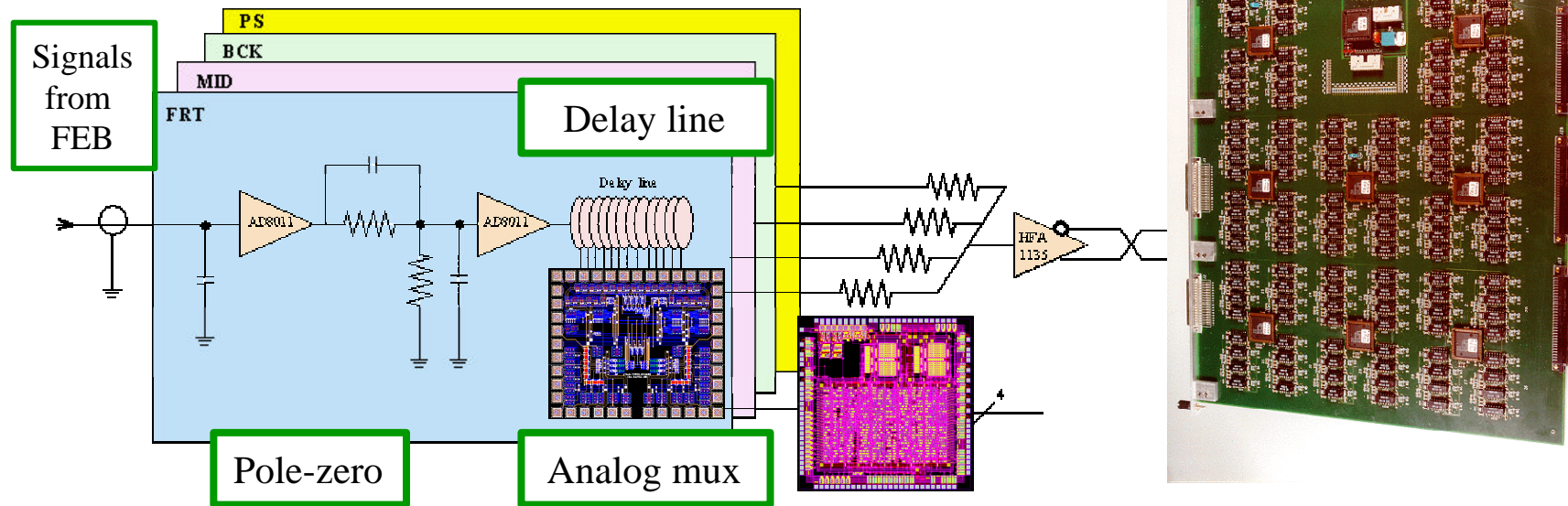
■ MUX (Multiplexer) (Grenoble) [cf. talk by D. Dzahini]

- Data formatting for Glink serializer (32bits 40MHz ? 16bits 80MHz)
- 18 mm² chip, received Mar 01. **yield : 88%.**
- **SEE** test up to ~ 10¹³ N (20 MeV) : negligible compared to Glink
- Iterated in may 01 to remove dual mux for single Glink



Tower builder : overview

- **Analog summation to form LVL1 towers (Saclay)**

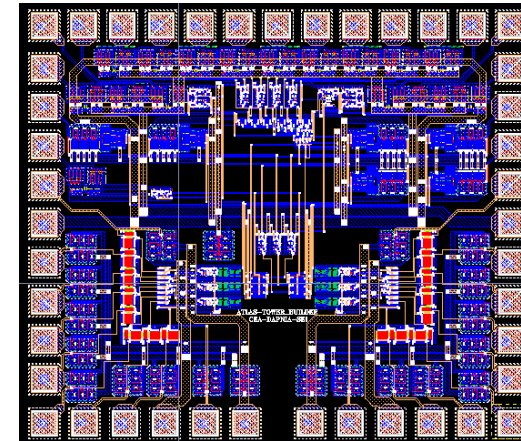


- **Milestones : same as calib**

- Oct 02 : 2 final boards
- Dec 02 : PRR

TBB : analog multiplexer

- **Analog multiplexer (BiMUX) : DMILL (Saclay)**
 - previous COTS (DG358) failed at 170 Gy
 - Prototype DMILL chip realized in 1998
 - 8 big CMOS switches + control logic (registers)
 - area : 4.6mm² ; yield : 80%
 - 32 chips per board ? 8,000 chips needed
 - Irradiated to 2 kGy and 310¹³ N.
 - SEU test showed no error up to ~ 10¹⁷ N (20 MeV)
 - Full production planned in 2001 or 2002



Shared DMILL wafers

- **Analog reticle**

- 52 opamps
- 25 BiMUX
- 2 DAC

- **13 wafers needed**

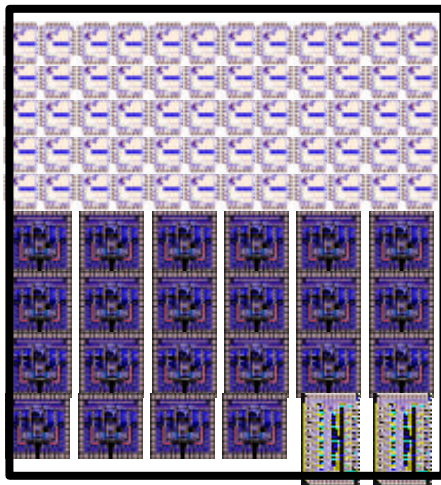
- **Cost : ~ 150 k\$**

- **Digital reticle**

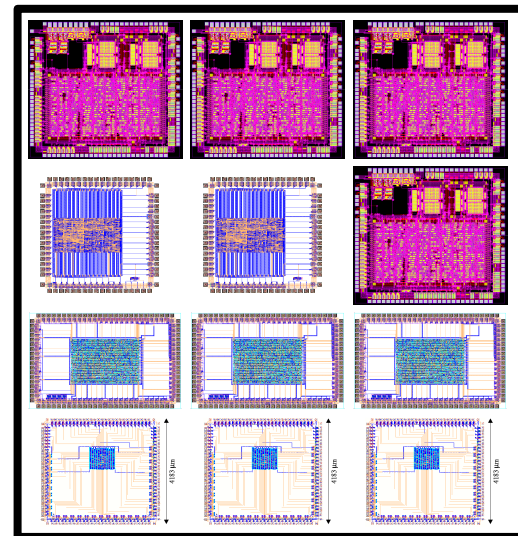
- 4 SPAC
- 2 calib logic
- 3 Configuration controllers
- 3 MUX

- **20 wafers necessary**

- **Cost : ~ 200 k\$**



18 mm



Summary of LArG DMILL chips

Chip	Area (mm ²)	Min chips required	OK /tested	Yield	Iteration out	Comments
SCA	30	54 000	1643/2543	65%	None	final
Gain select.	21	13 300	27/29	93%		DSM alternative
SCA contr.	80	3 300	28/40	70%		DSM alternative
FEB config	20	1 650	37/40	93%	None	final
DMUX	18	1 650	15/17	88%	nov 01	Remove dual
Calib logic	16.4	700	3/3	100%	nov 01	Fix initialization
SPAC slave	27	2 500	17/18	94%	feb 02	Mitigate SEU
Opamp	3	17 000	26/37*	70%*	nov 01	Add HF switch
DAC	6.3	130	18/19	94%	feb 02	Fix reference
Delay	6.5	260			None	final
TTCRx		2 100			None	final
BiMUX	4.6	8 320	65/80	81%	None	final

12 sept 2001 * within $\pm 100 \mu\text{V}$ C. de La Taille

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Summary

- **10 DMILL chips designed and produced in 2000-2001**
 - 3 MPW (MPW 471, MPW 511, MPW 533)
 - 1 full engineering run (SCA)

- **7 digital chips**
 - **Yield > 80%**
 - All designs final
 - 2 chips have 0.25 μm DSM alternatives (SCAC, Gain select.) ? **Choice in Oct 01**

- **3 analog chips**
 - Good performance (offset, leakage...)
 - **Yield > 65%**

- **250 wafers needed for ATLAS in 2002**
 - ~ 200 for the SCA, PRR in oct 2001
 - 33 shared wafers for 8 different chips : **packaging issues**